N-channel TrenchMOS standard level FET

**Product data sheet** 

### 1. General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

### 2. Features and benefits

- AEC Q101 compliant
- Low conduction losses due to low on-state resistance
- Suitable for standard level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

# 3. Applications

- 12 V, 24 V and 42 V loads
- Automotive systems
- General purpose power switching
- Motors, lamps and solenoids

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	75	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 1</u> ; <u>Fig. 3</u>		-	-	69	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	-	158	W
Static charact	eristics				'		
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; Fig. 11; Fig. 12		-	12.6	14	mΩ
Dynamic char	acteristics						
$Q_{GD}$	gate-drain charge	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; V_{DS} = 60 \text{ V};$ $T_j = 25 \text{ °C}; Fig. 13$		-	15	-	nC
Avalanche ruggedness							
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	$I_D$ = 69 A; $V_{sup} \le$ 75 V; $R_{GS}$ = 50 Ω; $V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; unclamped		-	-	136	mJ



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# 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol	
1	G	gate	mb	D I	
2	D	drain[1]			
3	S	source			G T A
mb	D	mounting base; connected to drain	1 3	mbb076 S	
			DPAK (SOT428)		

[1] It is not possible to make a connection to pin 2

# 6. Ordering information

Table 3. Ordering information

Type number	Package	je					
	Name	Description	Version				
BUK7214-75B	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428				

# 7. Marking

Table 4. Marking codes

Type number	Marking code
BUK7214-75B	BUK7214-75B

# 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	75	V
$V_{DGR}$	drain-gate voltage	$R_{GS}$ = 20 k $\Omega$	-	75	V
V <sub>GS</sub>	gate-source voltage		-20	20	V
I <sub>D</sub>	drain current	T <sub>mb</sub> = 25 °C; V <sub>GS</sub> = 10 V; <u>Fig. 1</u> ; <u>Fig. 3</u>	-	69	Α
		T <sub>mb</sub> = 100 °C; V <sub>GS</sub> = 10 V; <u>Fig. 1</u>	-	49	Α
I <sub>DM</sub>	peak drain current	$T_{mb}$ = 25 °C; pulsed; $t_p \le 10 \mu s$ ; Fig. 3	-	276	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>	-	158	W

BUK7214-75B

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Symbol	Parameter	Conditions	Min	Max	Unit
T <sub>stg</sub>	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
Source-drai	in diode				
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	-	69	Α
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$	-	276	Α
Avalanche i	ruggedness				
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$I_D$ = 69 A; $V_{sup} \le 75$ V; $R_{GS}$ = 50 Ω; $V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; unclamped	-	136	mJ

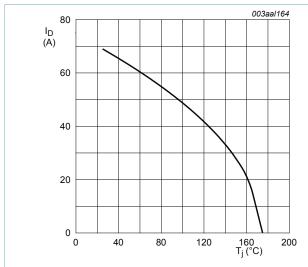


Fig. 1. Continuous drain current as a function of mounting base temperature

$$V_{GS} \ge 10 V$$

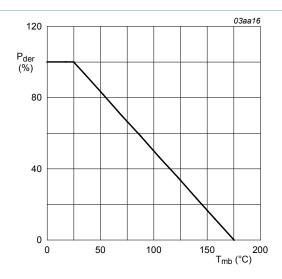


Fig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{\textit{der}} = \frac{P_{\textit{tot}}}{P_{\textit{tot}(25^{\circ}\textit{C})}} \times 100 \%$$

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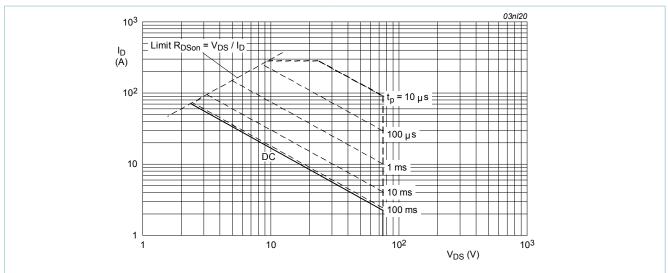


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

$$T_{mb} = 25^{\circ}C; I_{DM}$$
 is single pulse

### 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	Fig. 4	-	-	0.95	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient		-	71.4	-	K/W

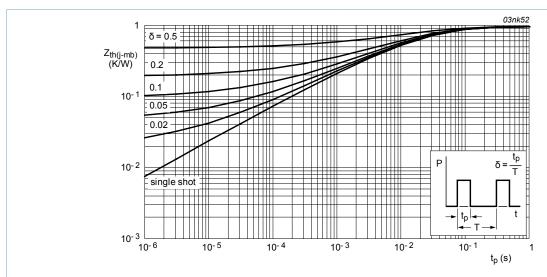


Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

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# 10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V <sub>(BR)DSS</sub>	drain-source	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	75	-	-	V
	breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 ^{\circ}\text{C}$	70	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ Fig. 10	0.9	-	-	V
		$I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 25 °C; Fig. 10	2	3	4	V
		$I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = -55 °C; Fig. 10	-	-	4.4	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 75 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 175 °C	-	-	500	μA
		V <sub>DS</sub> = 75 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	0.02	1	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
		V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
R <sub>DSon</sub> drain-source on-state resistance		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 175 °C; Fig. 11; Fig. 12	-	-	33	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; Fig. 11; Fig. 12	-	12.6	14	mΩ
Dynamic ch	naracteristics					
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 60 V; V <sub>GS</sub> = 10 V;	-	41	-	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C; <u>Fig. 13</u>	-	9	-	nC
$Q_{GD}$	gate-drain charge		-	15	-	nC
C <sub>iss</sub>	input capacitance	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 25 V; f = 1 MHz;	-	1959	2612	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 14</u>	-	326	391	pF
C <sub>rss</sub>	reverse transfer capacitance		-	159	218	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 25 V; $R_L$ = 1.2 $\Omega$ ; $V_{GS}$ = 10 V;	-	18	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)}$ = 10 Ω; $T_j$ = 25 °C	-	114	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	52	-	ns
t <sub>f</sub>	fall time		-	45	-	ns
L <sub>D</sub>	internal drain inductance	measured from drain to centre of die ; $T_j$ = 25 °C	-	2.5	-	nH
L <sub>S</sub>	internal source inductance	measured from source lead to source bond pad ; T <sub>i</sub> = 25 °C	-	7.5	-	nH

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Source-drain diode							
V <sub>SD</sub>	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}; Fig. 15$		-	0.85	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S = 20 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s};$		-	74	-	ns
Q <sub>r</sub>	recovered charge	$V_{GS} = -10 \text{ V}; V_{DS} = 30 \text{ V}; T_j = 25 \text{ °C}$		-	94	-	nC

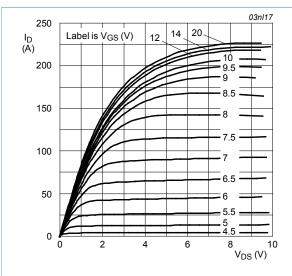


Fig. 5. Output characteristics: drain current as a function of drain-source voltage; typical values

$$T_j = 25^{\circ}C; t_p = 300\mu s$$

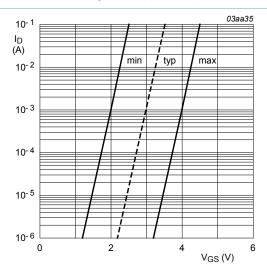


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

$$T_j = 25 \,^{\circ}C; V_{DS} = 5V$$

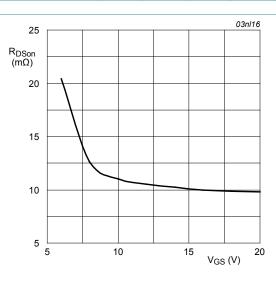


Fig. 6. Drain-source on-state resistance as a function of gate-source voltage; typical values

$$T_j = 25^{\circ}C; I_D = 25A$$

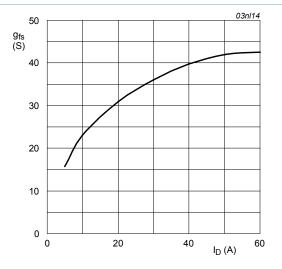


Fig. 8. Forward transconductance as a function of drain current; typical values

$$T_j = 25^{\circ}C; V_{DS} = 25V$$

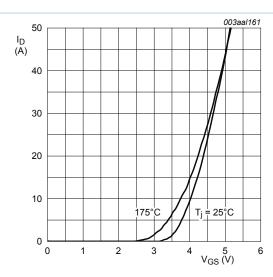


Fig. 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values

$$V_{DS} = 12V$$

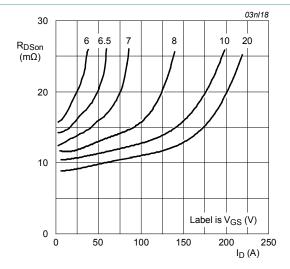


Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

$$T_j = 25^{\circ}C; t_p = 300\mu s$$

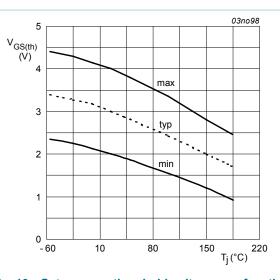


Fig. 10. Gate-source threshold voltage as a function of junction temperature

$$I_D = 1 mA; V_{DS} = V_{GS}$$

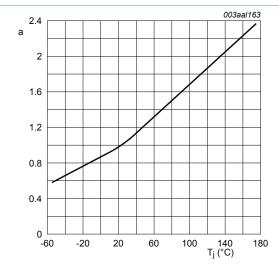


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon (25^{\circ}C)}}$$

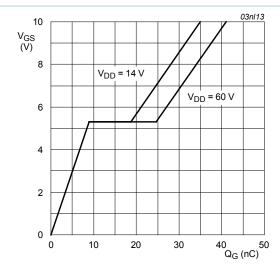


Fig. 13. Gate-source voltage as a function of gate charge; typical values

$$T_j = 25^{\circ}C; I_D = 25A$$

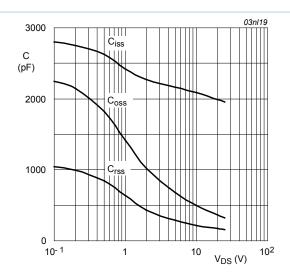


Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$V_{GS} = 0V; f = 1MHz$$

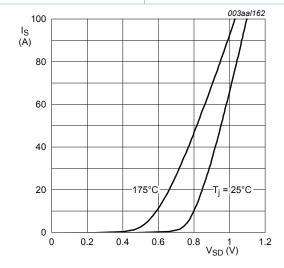


Fig. 15. Source current as a function of source-drain voltage; typical values

$$V_{GS} = 0V$$

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# 11. Package outline

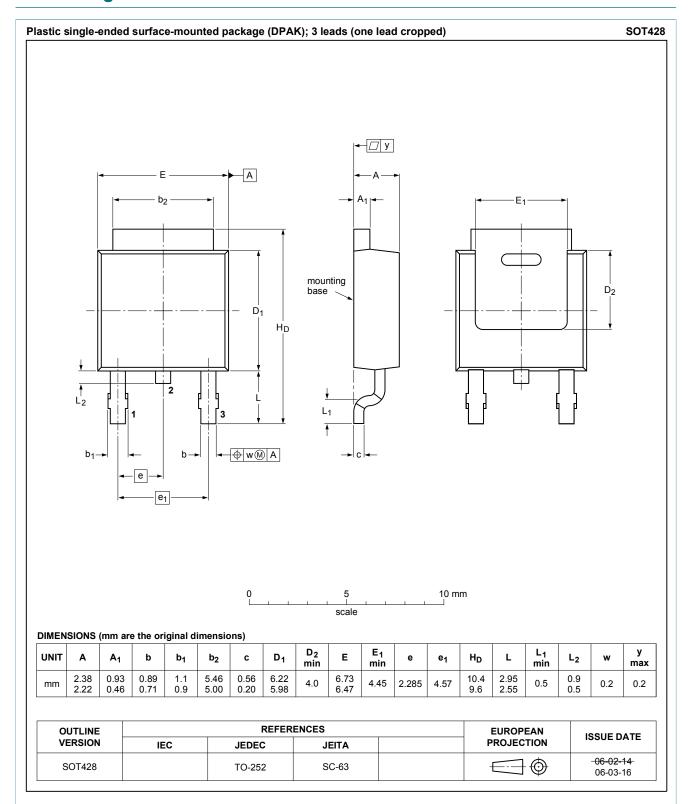


Fig. 16. Package outline DPAK (SOT428)

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